Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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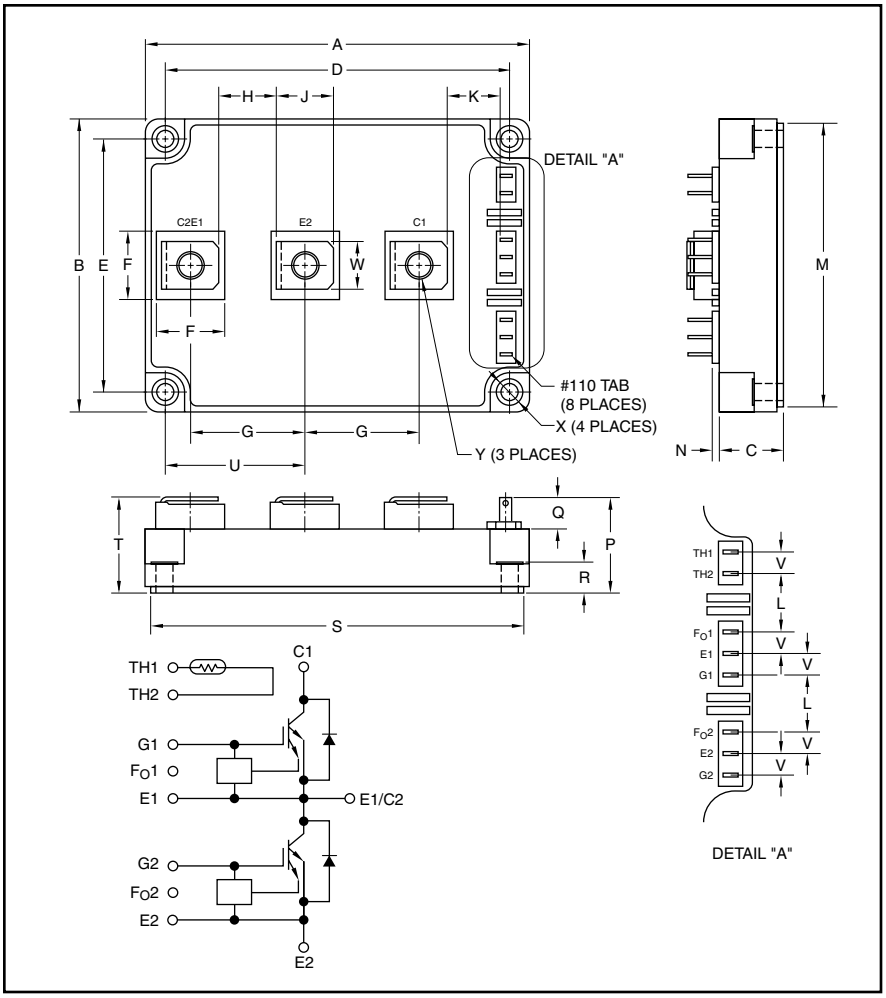
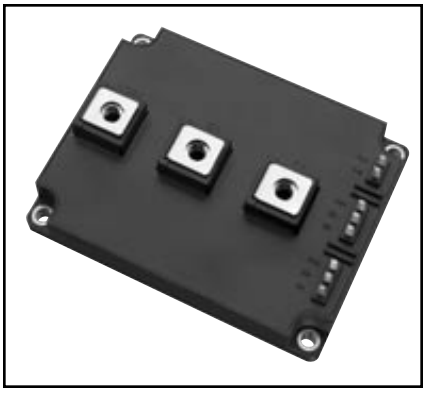
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Powerex, Inc., 200 E. Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

Dual IGBTMOD™ Compact IGBT Series Module

600 Amperes/1200 Volts





Description:
Powerex Dual IGBTMOD™ Compact IGBT Series Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Over-Current and Over-Temperature Protection
- ☐ Low $V_{CE(sat)}$
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:
Example: Select the complete part number from the table below -i.e. MG600Q2YS60A is a 1200V (V_{CES}), 600 Ampere Dual IGBTMOD™ Compact IGBT Series Module.

Type	Current Rating Amperes	V_{CES} Volts (x 10)
MG	600	120

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.92±0.04	125.0±1.0
B	3.78±0.04	96.0±1.0
C	0.84±0.04	21.3±1.0
D	4.49±0.03	113.0±0.8
E	3.30±0.03	84.0±0.8
F	0.86±0.04	22.0±1.0
G	1.46±0.04	37.0±1.0
H	0.75±0.04	19.0±1.0
J	0.71±0.04	18.0±1.0
K	0.73±0.04	18.6±1.0
L	0.59±0.04	15.0±1.0
M	3.66±0.03	93.0±0.8

Dimensions	Inches	Millimeters
N	0.07±0.04	1.8±1.0
P	1.24±0.04	31.5±1.0
Q	0.40±0.03	10.2±0.8
R	0.34±0.03	8.7±0.8
S	4.92±0.04	125.0±1.0
T	1.24-0.01/+0.04	31.5+2.0/-0.8
U	1.81±0.04	46.0±1.0
V	0.22±0.04	5.6±1.0
W	0.63±0.03	16.0±0.8
X	0.21 Dia.	5.5 Dia.
Y	M8 Metric	M8

MG600Q2YS60A
Dual IGBTMOD™
Compact IGBT Series Module
600 Amperes/1200 Volts

Absolute Maximum Ratings, T_j = 25°C unless otherwise specified

Characteristics	Symbol	MG600Q2YS60A	Units
Collector-Emitter Voltage	V_{CES}	1200	Volts
Gate-Emitter Voltage	V_{GES}	±20	Volts
Collector Current (DC)	I_C	600	Amperes
Forward Current (DC)	I_F	600	Amperes
Collector Dissipation (T_C = 25°C)	P_C	4300	Watts
Power Device Junction Temperature	T_j	-20 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Mounting Torque, M5 Mounting Screws	—	27	in-lb
Mounting Torque, M8 Main Terminal Screws	—	88	in-lb
Module Weight (Typical)	—	680	Grams
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal	V_{ISO}	2500	Volts

Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Gate Leakage Current	I_{GES}	V_{GE} = ±20V, V_{CE} = 0V	—	—	±10	µA
Collector Cutoff Current	I_{CES}	V_{CE} = 1200V, V_{GE} = 0V	—	—	1.0	mA
Gate-Emitter Cutoff Voltage	$V_{GE(off)}$	I_C = 600mA, V_{CE} = 5V	6.0	6.7	8.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C = 600A, T_j = 25°C	—	2.7	3.1	Volts
		V_{GE} = 15V, I_C = 600A, T_j = 125°C	—	3.2	3.5	Volts
Input Capacitance	C_{ies}	V_{CE} = 10V, V_{GE} = 0V, f = 1MHz	—	41000	—	pF
Gate-Emitter Voltage	V_{GE}		13.0	15.0	17.0	Volts
Gate Resistance	R_G		7.5	—	15.0	Ω
Inductive Load	$t_{d(on)}$	V_{CC} = 600V, I_C = 600A, V_{GE} = ±15V, R_G = 7.5Ω	—	0.3	—	µs
Switching	t_r		—	0.2	—	µs
Times	t_{on}		—	0.5	—	µs
	$t_{d(off)}$		—	1.3	—	µs
	t_f		—	0.1	0.3	µs
	t_{off}		—	1.4	—	µs
Forward Voltage	V_F	I_F = 600A, V_{GE} = 0V, T_j = 25°C	—	2.2	3.2	Volts
		I_F = 600A, V_{GE} = 0V, T_j = 125°C	—	2.0	—	Volts
Reverse Recovery Time	t_{rr}	I_F = 600A, V_{GE} = -15V, di/dt = 2000A/µs	—	0.3	0.5	µs
Junction to Case Thermal Resistance	$R_{th(j-c)Q}$	IGBT (Per 1/2 Module)	—	—	0.029	°C/Watt
	$R_{th(j-c)D}$	FWDi (Per 1/2 Module)	—	—	0.056	°C/Watt
RTC Operating Current	I_{rtc}	T_j = 25°C	1200	—	—	Amperes

MG600Q2YS60A
Dual IGBTMOD™
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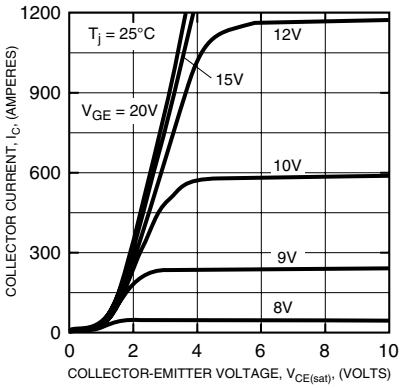
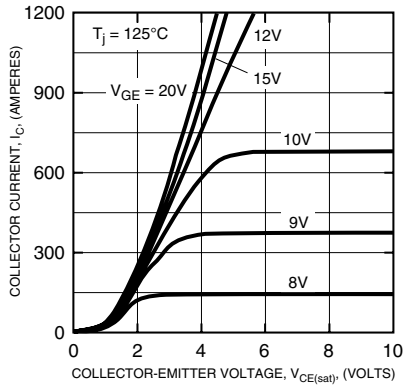
600 Amperes/1200 Volts

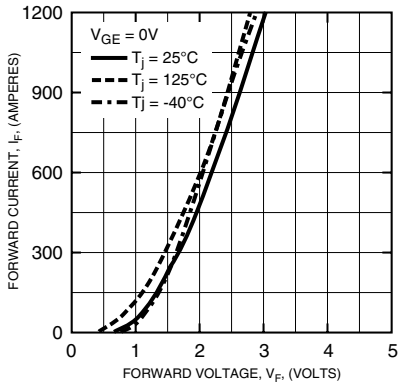
OUTPUT CHARACTERISTICS (TYPICAL)



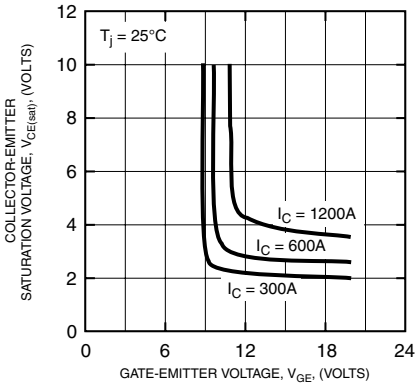
OUTPUT CHARACTERISTICS (TYPICAL)



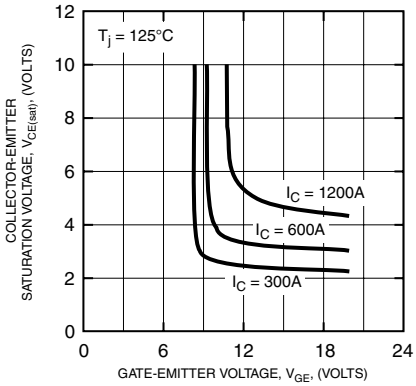
FREE-WHEEL CHARACTERISTICS (TYPICAL)



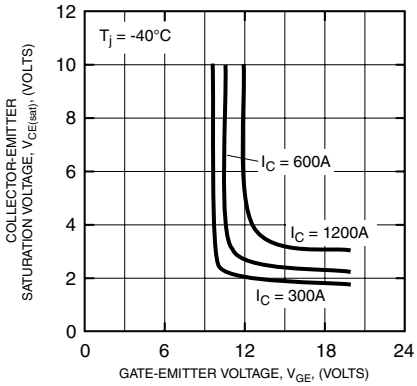
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



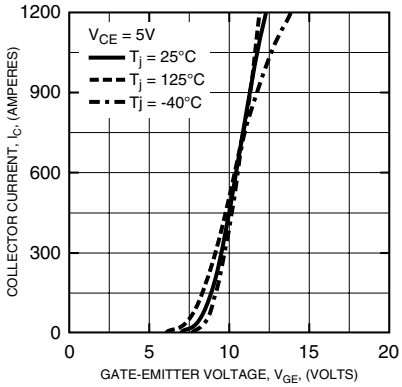
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



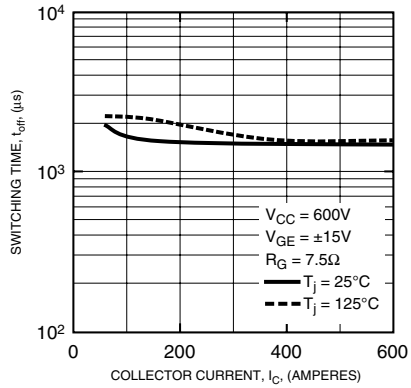
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



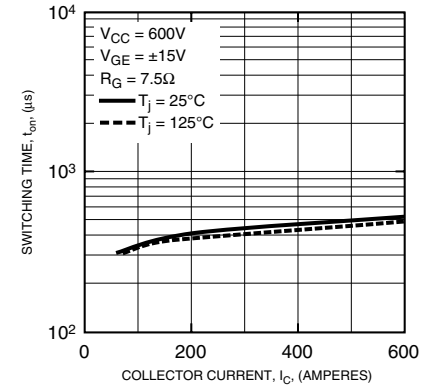
TRANSFER CHARACTERISTICS (TYPICAL)



TURN-OFF TIME VS. COLLECTOR CURRENT (TYPICAL)

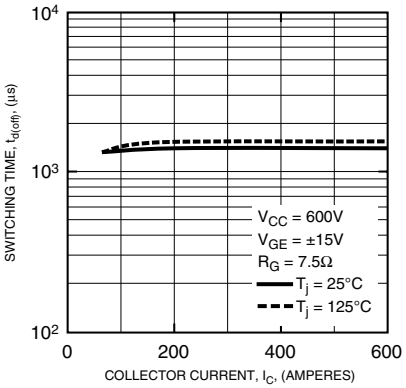


TURN-ON TIME VS. COLLECTOR CURRENT (TYPICAL)

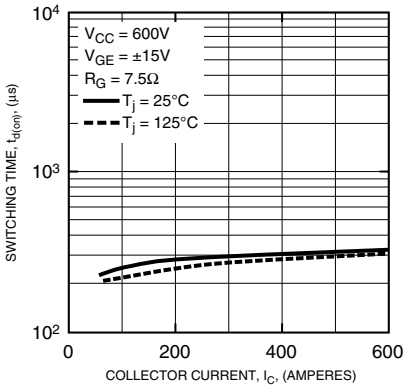


MG600Q2YS60A
Dual IGBTMOD™
Compact IGBT Series Module
600 Amperes/1200 Volts

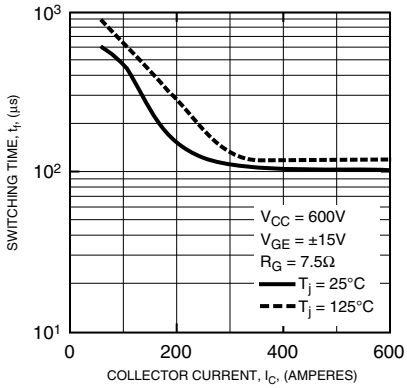
TURN-OFF DELAY TIME VS. COLLECTOR CURRENT (TYPICAL)



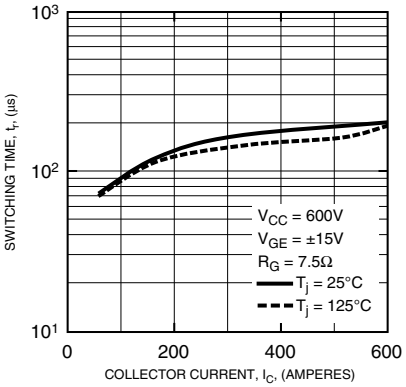
TURN-ON DELAY TIME VS. COLLECTOR CURRENT (TYPICAL)



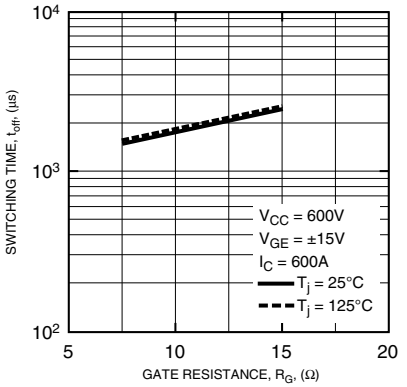
FALL TIME VS. COLLECTOR CURRENT (TYPICAL)



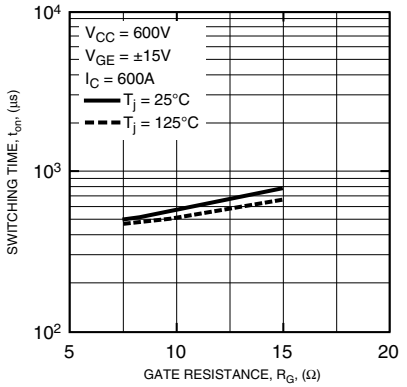
RISE TIME VS. COLLECTOR CURRENT (TYPICAL)



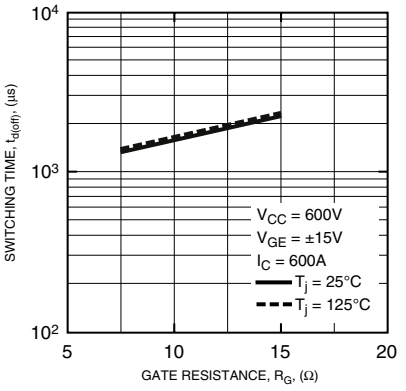
TURN-OFF TIME VS. GATE RESISTANCE (TYPICAL)



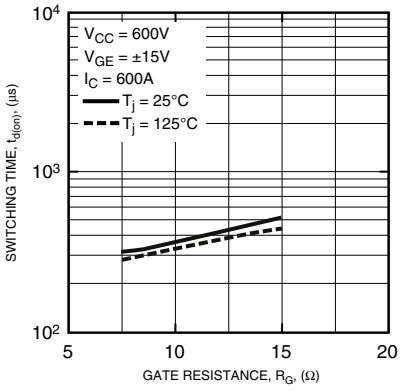
TURN-ON TIME VS. GATE RESISTANCE (TYPICAL)



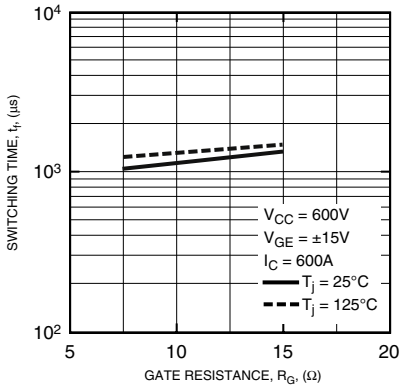
TURN-OFF DELAY TIME VS. GATE RESISTANCE (TYPICAL)



TURN-ON DELAY TIME VS. GATE RESISTANCE (TYPICAL)

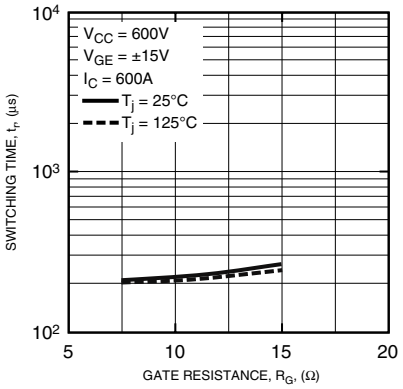


FALL TIME VS. GATE RESISTANCE (TYPICAL)

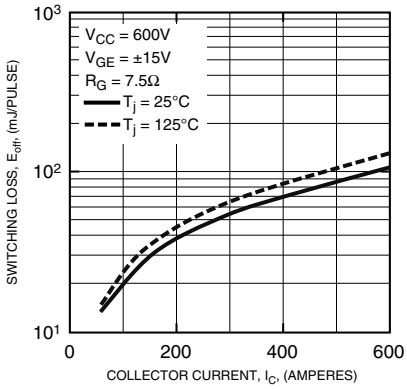


MG600Q2YS60A
Dual IGBTMOD™
Compact IGBT Series Module
600 Amperes/1200 Volts

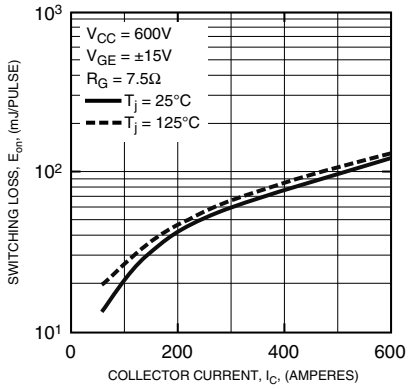
RISE TIME VS. GATE RESISTANCE (TYPICAL)



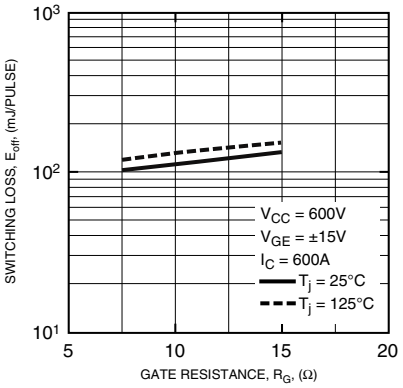
SWITCHING LOSS (OFF) VS. COLLECTOR CURRENT (TYPICAL)



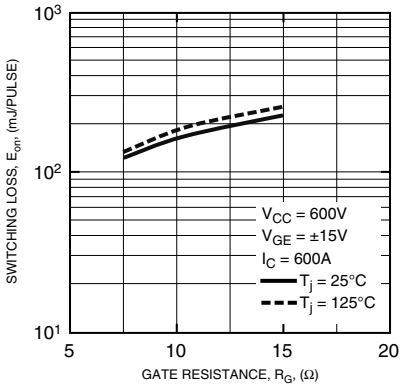
SWITCHING LOSS (ON) VS. COLLECTOR CURRENT (TYPICAL)



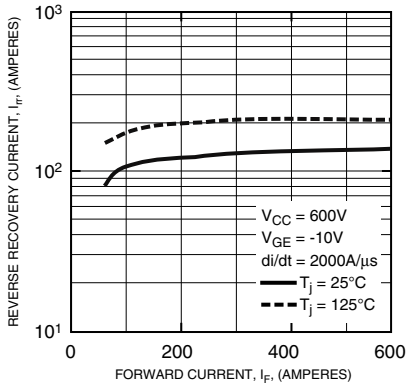
SWITCHING LOSS (OFF) VS. GATE RESISTANCE (TYPICAL)



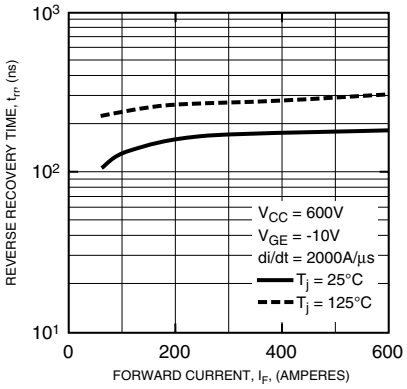
SWITCHING LOSS (ON) VS. GATE RESISTANCE (TYPICAL)



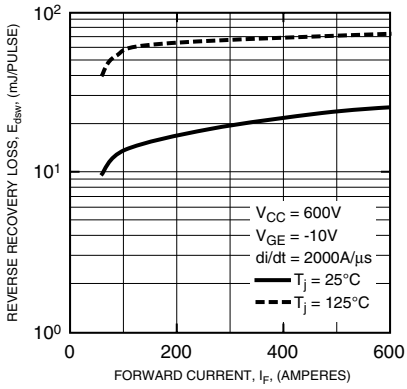
REVERSE RECOVERY CURRENT (TYPICAL)



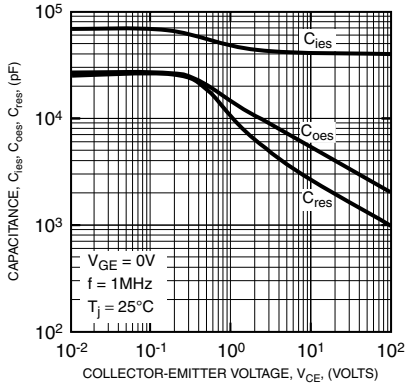
REVERSE RECOVERY TIME (TYPICAL)



REVERSE RECOVERY LOSS VS. FORWARD CURRENT (TYPICAL)

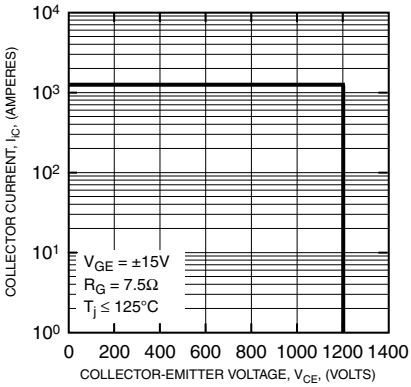


CAPACITANCE VS. COLLECTOR-EMITTER VOLTAGE (TYPICAL)

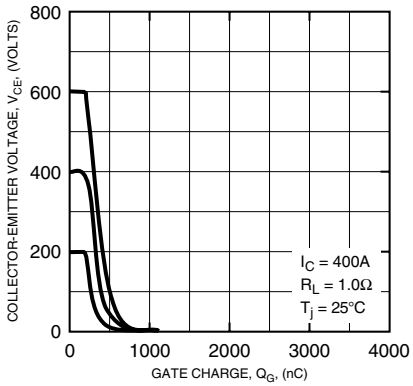


MG600Q2YS60A
Dual IGBTMOD™
Compact IGBT Series Module
600 Amperes/1200 Volts

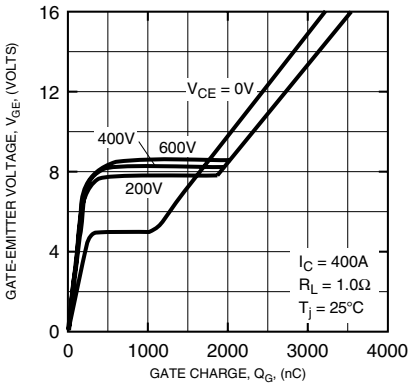
REVERSE BIAS SAFE OPERATION AREA (TYPICAL)



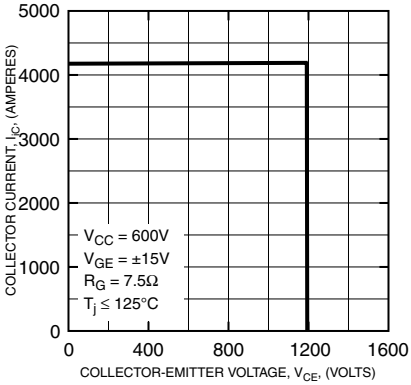
COLLECTOR-EMITTER VOLTAGE VS. GATE CHARGE (TYPICAL)



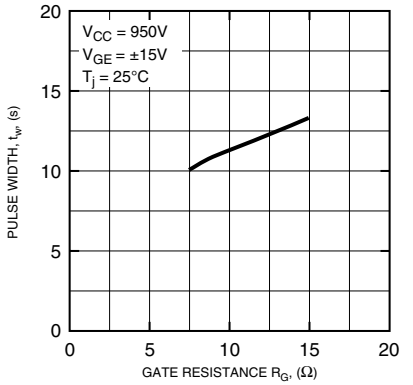
GATE-EMITTER VOLTAGE VS. GATE CHARGE (TYPICAL)



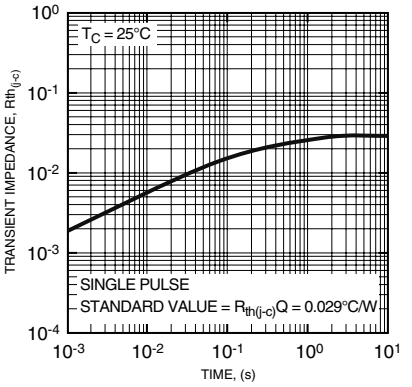
SHORT CIRCUIT SAFE OPERATING AREA (TYPICAL)



SHORT CIRCUIT PULSE WIDTH VS. GATE RESISTANCE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (FWDi)